WHAT IS CLAIMED IS:

1. A pattern forming method comprising:

an exposure step of exposing a photosensitive film to laser light; and

a development step of developing the photosensitive film after the exposure to obtain a pattern,

wherein the photosensitive film contains at least one precursor selected from the group consisting of a polyimide precursor and a polybenzoxazole precursor, and an onium salt.

2. The pattern forming method according to claim 1,

wherein a wavelength of the laser light is 250 to 550 nm.

3. The pattern forming method according to claim 1 or 2,

wherein the photosensitive film further contains a compound having a plurality of carboxy groups and having a molecular weight of 1,000 or less.

4. The pattern forming method according to any one of claims 1 to 3,

wherein the photosensitive film further contains a compound having a sulfurous ester structure.

5. The pattern forming method according to any one of claims 1 to 4, further comprising a curing step of heating the pattern to obtain a cured pattern, after the development step.

6. The pattern forming method according to any one of claims 1 to 5,

wherein a cation in the onium salt includes at least one cation selected from the group consisting of a tetraalkylammonium cation, a sulfonium cation, and an iodonium cation.

7. The pattern forming method according to any one of claims 1 to 6,

wherein the onium salt contains an ammonium cation as a cation, and the onium salt contains an anion of which a conjugate acid has a pKa of 1.8 or less, as an anion.

8. The pattern forming method according to any one of claims 1 to 7,

wherein the photosensitive film further contains a Group 4 element-containing

compound is further contained.

9. The pattern forming method according to claim 8,

wherein the Group 4 element-containing compound is a photoradical generator.

10. The pattern forming method according to claim 8 or 9,

wherein the Group 4 element-containing compound is an organic compound containing at least one selected from the group consisting of a titanium atom, a zirconium atom, and a hafnium atom.

11. The pattern forming method according to any one of claims 8 to 10,

wherein the Group 4 element-containing compound includes at least one selected from the group consisting of metallocene and a metallocene derivative.

12. The pattern forming method according to any one of claims 1 to 11,

wherein the photosensitive film is a photosensitive film formed by slit coating.

13. The pattern forming method according to any one of claims 1 to 12,

wherein the photosensitive film is formed on a rectangular base material.

14. A photosensitive resin composition comprising:

at least one precursor selected from the group consisting of a polyimide precursor and a polybenzoxazole precursor; and

an onium salt,

wherein the photosensitive resin composition is used for forming the photosensitive film in the pattern forming method according to any one of claims 1 to 13.

15. A cured film formed from the photosensitive resin composition according to claim 14.

16. The cured film according to claim 15,

wherein the cured film is used as an interlayer insulating film for a rewiring layer.

17. A laminate comprising two or more layers of the cured films according to claim 15 or 16.

18. The laminate according to claim 17, further comprising a metal layer between the cured films.

19. A device comprising the cured film according to claim 15 or 16 or the laminate according to claim 17 or 18.